

Amendments to the specification

Please replace the abstract of the Invention at page 14 of the original application with the following rewritten paragraph. In the rewritten paragraph, the words “(Fig. 1)” and “BUR920020076US2” have been removed.

--A programmable device includes a substrate (10); an insulator (13) on the substrate; an elongated semiconductor material (12) on the insulator, the elongated semiconductor material having first and second ends, and an upper surface S; the first end (12a) is substantially wider than the second end (12b), and a metallic material is disposed on the upper surface; the metallic material being physically migratable along the upper surface responsive to an electrical current I flowable through the semiconductor material and the metallic material.--

Please replace the paragraph at page 7, lines 22 – 30 of the original application with the following rewritten paragraph:

--FIG. 11 shows top views of the fuse, showing the fuse link width equal to 0.196 μm , and a fuse link (central portion) length of 1.862 μm . Of course, fuse link widths can be $[[<]]$ less than 0.2 μm , i.e., 1 μm and below. It is important that all of the poly (12, 21) sits over the isolation (13), such that a thermal path is directed towards heating the metallic silicide (40) during a programming event. Metallic silicide is migrated from the huge negative terminal source and flows to the positive source via an electron wind. The positive source area must be $[[<]]$ less than the negative source area to allow the silicide to recrystallize within the

underlying poly, and to heat the poly uniformly at the recrystalline point L so as to break (90) the line (12, 21) through heating.--

Please replace the paragraph at page 7, line 32 – page 8, line 7 of the original application with the following rewritten paragraph:

-- FIGS. 12-15 show top schematic conceptual views useful for understanding the programming process of the present invention. The silicide (40) is driven from the negative terminal and piles up at the positive terminal where the polysilicon is heated and subsequently forms an open circuit, where $\Delta R_p=0$. A cross section shows the recrystallization of the silicide near (proximate) the point of programming versus the original "skin" silicide layer (40) over the negative terminal. No damage of the surrounding oxide is evident. It is an important criterion that the resistivity of the metallic silicide (40) be $[\leq]$ less than that of the underlying polysilicon (12, 21). The materials described as examples meet this criterion.--